Not Recommended for New Design
Please Use FMMT491

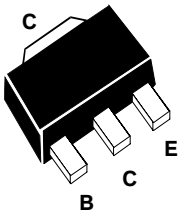
SOT89 NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

ISSUE 3 – FEBRUARY 1996 ✪

BSR41
BSR43

COMPLEMENTARY TYPES – BSR43 - BSR33
BSR41 - BSR31

PARTMARKING DETAIL – BSR43 - AR4
BSR41 - AR2



SOT89

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	BSR41	BSR43	UNIT
Collector-Base Voltage	V_{CBO}	70	90	V
Collector-Emitter Voltage	V_{CEO}	60	80	V
Emitter-Base Voltage	V_{EBO}	5		V
Peak Pulse Current	I_{CM}	2		A
Continuous Collector Current	I_C	1		A
Base Current	I_B	100		mA
Power Dissipation at T_{amb}=25°C	P_{TOT}	1		W
Operating and Storage Temperature Range	T_j:T_{stg}	-65 to +150		°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage BSR43 BSR41	$V_{(BR)CBO}$	90 70		V	I_C=100µA
Collector-Emitter Breakdown Voltage BSR43 BSR41	$V_{(BR)CEO}$	80 60		V	I_C=10mA *
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	I_E=10µA
Collector Cut-Off Current	I_{CBO}		100 50	nA µA	V_{CB}=60V V_{CB}=60V, Tamb =125°C
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25 0.5	V V	I_C =150mA, I_B =15mA I_C =500mA, I_B =50mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.0 1.2	V V	I_C =150mA, I_B =15mA I_C =500mA, I_B =50mA
Static Forward Current Transfer Ratio	h_{FE}	30 100 50	300		I_C =100µA, V_{CE} =5V I_C =100mA, V_{CE} =5V I_C =500mA, V_{CE} =5V
Collector Capacitance	C_c		12	pF	V_{CB} =10V, f=1MHz
Emitter Capacitance	C_e		90	pF	V_{EB} =0.5V, f=1MHz
Transition Frequency	f_T	100		MHz	I_C=50mA, V_{CE}=10V f =35MHz
Turn-On Time	T_{on}		250	ns	V_{CC}=20V, I_C =100mA I_{B1}=I_{B2}=5mA
Turn-Off Time	T_{off}		1000	ns	

*Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%
For typical characteristics graphs see FMMT493 datasheet.